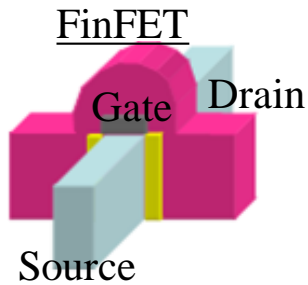
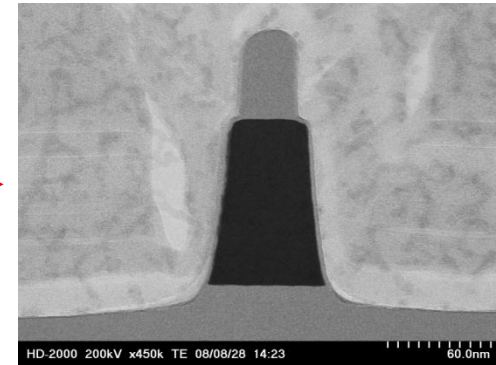
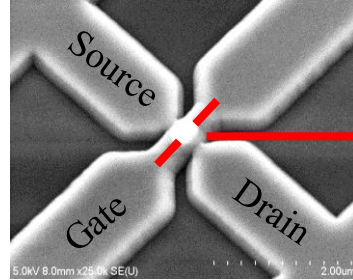


FinFET Fabrication Using Neutral Beam Oxidation

Cross-sectional TEM image of fin structure

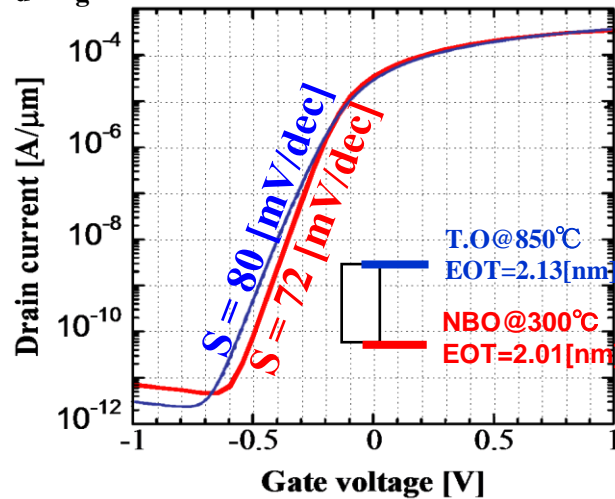


SEM image of FinFET

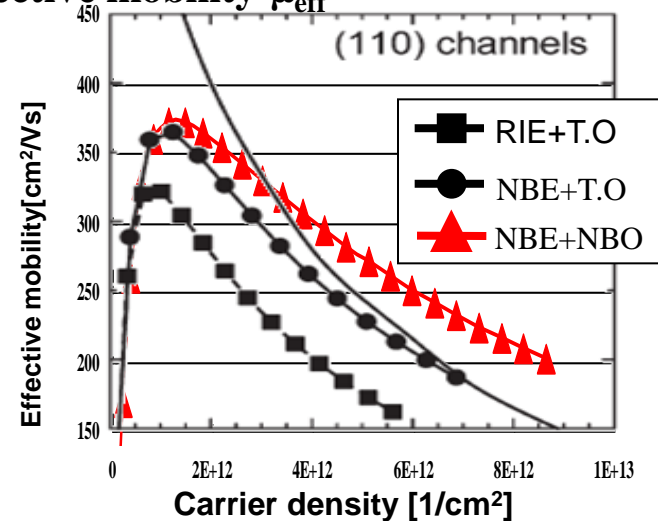


Gate oxide film; NBO (300°C) vs Thermal oxidation

I_d - V_g characteristic



Effective mobility μ_{eff}



Wada et al. Jpn. J. Appl. Phys. 49, 04DC17 (2010)

The S-slope and the effective mobility were improved in FinFET fabricated using NBO (300°C).